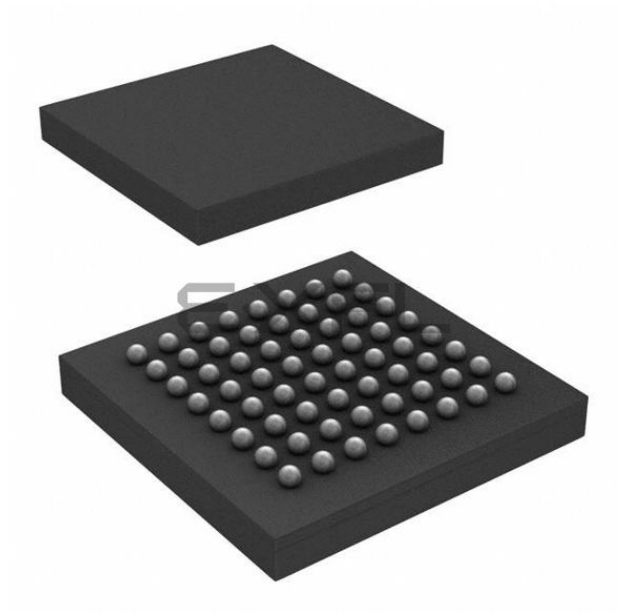

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-UFBGA
Supplier Device Package	64-UFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f091rch6tr

Both comparators can wake up from STOP mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

3.13 Touch sensing controller (TSC)

The STM32F091xB/xC devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists in charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage, this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate. For operation, one capacitive sensing GPIO in each group is connected to an external capacitor and cannot be used as effective touch sensing channel.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 5. Capacitive sensing GPIOs available on STM32F091xB/xC devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
1	TSC_G1_IO1	PA0	5	TSC_G5_IO1	PB3
	TSC_G1_IO2	PA1		TSC_G5_IO2	PB4
	TSC_G1_IO3	PA2		TSC_G5_IO3	PB6
	TSC_G1_IO4	PA3		TSC_G5_IO4	PB7
2	TSC_G2_IO1	PA4	6	TSC_G6_IO1	PB11
	TSC_G2_IO2	PA5		TSC_G6_IO2	PB12
	TSC_G2_IO3	PA6		TSC_G6_IO3	PB13
	TSC_G2_IO4	PA7		TSC_G6_IO4	PB14
3	TSC_G3_IO1	PC5	7	TSC_G7_IO1	PE2
	TSC_G3_IO2	PB0		TSC_G7_IO2	PE3
	TSC_G3_IO3	PB1		TSC_G7_IO3	PE4
	TSC_G3_IO4	PB2		TSC_G7_IO4	PE5
4	TSC_G4_IO1	PA9	8	TSC_G8_IO1	PD12
	TSC_G4_IO2	PA10		TSC_G8_IO2	PD13
	TSC_G4_IO3	PA11		TSC_G8_IO3	PD14
	TSC_G4_IO4	PA12		TSC_G8_IO4	PD15

Table 6. Number of capacitive sensing channels available on STM32F091xB/xC devices

Analog I/O group	Number of capacitive sensing channels		
	STM32F091Vx	STM32F091Rx	STM32F091Cx
G1	3	3	3
G2	3	3	3
G3	3	3	2
G4	3	3	3
G5	3	3	3
G6	3	3	3
G7	3	0	0
G8	3	0	0
Number of capacitive sensing channels	24	18	17

3.14 Timers and watchdogs

The STM32F091xB/xC devices include up to six general-purpose timers, two basic timers and an advanced control timer.

Table 7 compares the features of the different timers.

Table 7. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	3
General purpose	TIM2	32-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM14	16-bit	Up	integer from 1 to 65536	No	1	-
	TIM15	16-bit	Up	integer from 1 to 65536	Yes	2	1
	TIM16 TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	1
Basic	TIM6 TIM7	16-bit	Up	integer from 1 to 65536	Yes	-	-

Table 13. STM32F091xB/xC pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48					Alternate functions	Additional functions
M11	45	-	-	-	-	PE14	I/O	FT		SPI1_MISO, I2S1_MCK, TIM1_CH4	-
M12	46	-	-	-	-	PE15	I/O	FT		SPI1_MOSI, I2S1_SD, TIM1_BKIN	-
L10	47	G7	29	G3	21	PB10	I/O	FTf		SPI2_SCK, I2S2_CK, I2C2_SCL, USART3_TX, CEC, TSC_SYNC, TIM2_CH3	-
L11	48	H7	30	H3	22	PB11	I/O	FTf		USART3_RX, TIM2_CH4, EVENTOUT, TSC_G6_IO1, I2C2_SDA	-
F12	49	D5	31	H2	23	VSS	S	-		Ground	
G12	50	E5	32	H1	24	VDD	S	-		Digital power supply	
L12	51	H8	33	G2	25	PB12	I/O	FT		TIM1_BKIN, TIM15_BKIN, SPI2_NSS, I2S2_WS, USART3_CK, TSC_G6_IO2, EVENTOUT	-
K12	52	G8	34	F2	26	PB13	I/O	FTf		SPI2_SCK, I2S2_CK, I2C2_SCL, USART3_CTS, TIM1_CH1N, TSC_G6_IO3	-
K11	53	F8	35	G1	27	PB14	I/O	FTf		SPI2_MISO, I2S2_MCK, I2C2_SDA, USART3_RTS, TIM1_CH2N, TIM15_CH1, TSC_G6_IO4	-
K10	54	F7	36	F1	28	PB15	I/O	FT		SPI2_MOSI, I2S2_SD, TIM1_CH3N, TIM15_CH1N, TIM15_CH2	WKUP7, RTC_REFIN
K9	55	-	-	-	-	PD8	I/O	FT		USART3_TX	-
K8	56	-	-	-	-	PD9	I/O	FT		USART3_RX	-
J12	57	-	-	-	-	PD10	I/O	FT		USART3_CK	-
J11	58	-	-	-	-	PD11	I/O	FT		USART3_CTS	-

Table 13. STM32F091xB/xC pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48					Alternate functions	Additional functions
C5	91	C4	57	C5	41	PB5	I/O	FT		SPI1_MOSI, I2S1_SD, I2C1_SMBA, TIM16_BKIN, TIM3_CH2, USART5_CK_RTS	WKUP6
B5	92	D3	58	A5	42	PB6	I/O	FTf		I2C1_SCL, USART1_TX, TIM16_CH1N, TSC_G5_I03	-
B4	93	C3	59	B5	43	PB7	I/O	FTf		I2C1_SDA, USART1_RX, USART4_CTS, TIM17_CH1N, TSC_G5_IO4	-
A4	94	B4	60	C6	44	PF11-BOOT0	I/O	FT		-	Boot memory selection
A3	95	B3	61	A6	45	PB8	I/O	FTf		I2C1_SCL, CEC, TIM16_CH1, TSC_SYNC, CAN_RX	-
B3	96	A3	62	B6	46	PB9	I/O	FTf		SPI2_NSS, I2S2_WS, I2C1_SDA, IR_OUT, TIM17_CH1, EVENTOUT, CAN_TX	-
C3	97	-	-	-	-	PE0	I/O	FT		EVENTOUT, TIM16_CH1	-
A2	98	-	-	-	-	PE1	I/O	FT		EVENTOUT, TIM17_CH1	-
D3	99	D4	63	A7	47	VSS	S	-		Ground	
C4	100	E4	64	A8	48	VDD	S	-		Digital power supply	

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF.
   - These GPIOs must not be used as current sources (e.g. to drive an LED).
2. After the first RTC domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the RTC domain and RTC register descriptions in the reference manual.
3. PC6, PC7, PC8, PC9, PA8, PA9, PA10, PA11, PA12, PA13, PF6, PA14, PA15, PC10, PC11, PC12, PD0, PD1 and PD2 I/Os are supplied by VDDIO2
4. After reset, these pins are configured as SWDIO and SWCLK alternate functions, and the internal pull-up on the SWDIO pin and the internal pull-down on the SWCLK pin are activated.

Table 20. STM32F091xB/xC peripheral register boundary addresses

Bus	Boundary address	Size	Peripheral
	0x4800 1800 - 0x5FFF FFFF	~384 MB	Reserved
AHB2	0x4800 1400 - 0x4800 17FF	1 KB	GPIOF
	0x4800 1000 - 0x4800 13FF	1 KB	GPIOE
	0x4800 0C00 - 0x4800 0FFF	1 KB	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 KB	GPIOC
	0x4800 0400 - 0x4800 07FF	1 KB	GPIOB
	0x4800 0000 - 0x4800 03FF	1 KB	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 MB	Reserved
AHB1	0x4002 4000 - 0x4002 43FF	1 KB	TSC
	0x4002 3400 - 0x4002 3FFF	3 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
	0x4002 2000 - 0x4002 23FF	1 KB	Flash memory interface
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0400 - 0x4002 0FFF	3 KB	Reserved
	0x4002 0000 - 0x4002 03FF	1 KB	DMA
	0x4001 8000 - 0x4001 FFFF	32 KB	Reserved

Table 33. Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal

Symbol	Parameter	f_{HCLK}	Typical consumption in Run mode		Typical consumption in Sleep mode		Unit
			Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	
I_{DD}	Current consumption from V_{DD} supply	48 MHz	26.7	15.1	16.4	3.8	mA
		36 MHz	20.4	11.8	12.7	3.3	
		32 MHz	18.5	11.0	11.4	3.0	
		24 MHz	14.6	8.7	9.0	2.3	
		16 MHz	10.2	6.1	6.4	1.8	
		8 MHz	5.1	3.3	3.2	1.2	
		4 MHz	3.3	2.2	2.3	1.1	
		2 MHz	2.2	1.7	1.7	1.1	
		1 MHz	1.6	1.4	1.4	1.1	
		500 kHz	1.4	1.2	1.2	1.0	
I_{DDA}	Current consumption from V_{DDA} supply	48 MHz	172				µA
		36 MHz	131				
		32 MHz	119				
		24 MHz	93				
		16 MHz	67				
		8 MHz	2.7				
		4 MHz	2.7				
		2 MHz	2.7				
		1 MHz	2.7				
		500 kHz	2.7				

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 53: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt

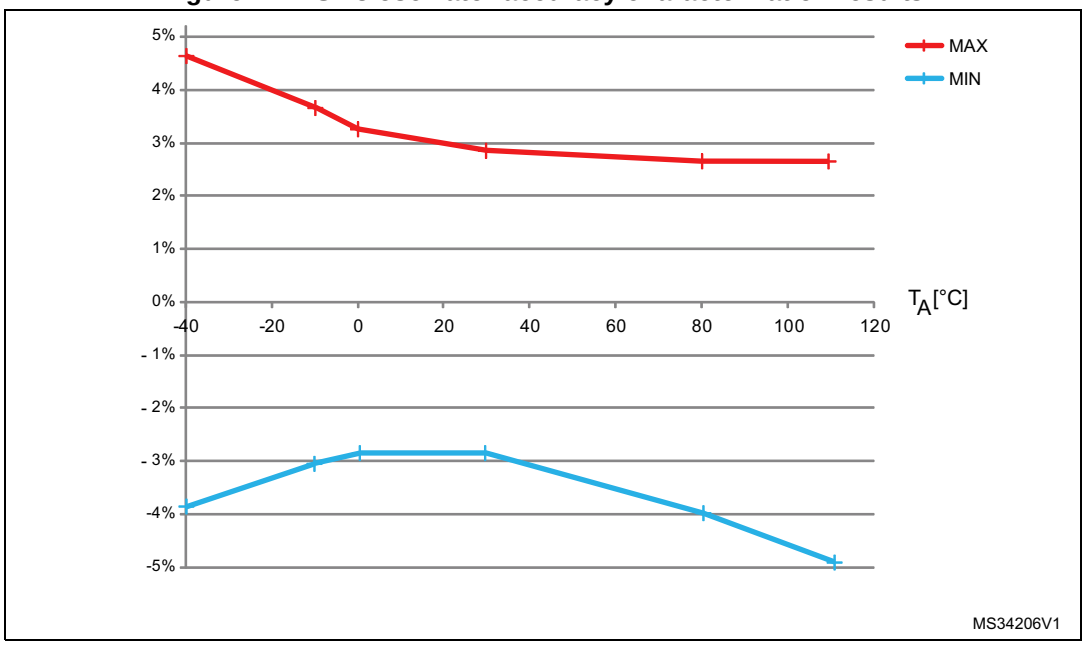
High-speed internal 48 MHz (HSI48) RC oscillator

Table 43. HSI48 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI48}	Frequency	-	-	48	-	MHz
TRIM	HSI48 user-trimming step	-	0.09(2)	0.14	0.2(2)	%
$DuCy_{(HSI48)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI48}	Accuracy of the HSI48 oscillator (factory calibrated)	T_A = –40 to 105 °C	-4.9(3)	-	4.7(3)	%
		T_A = –10 to 85 °C	-4.1(3)	-	3.7(3)	%
		T_A = 0 to 70 °C	-3.8(3)	-	3.4(3)	%
		T_A = 25 °C	-2.8	-	2.9	%
$t_{su(HSI48)}$	HSI48 oscillator startup time	-	-	-	6(2)	µs
$I_{DDA(HSI48)}$	HSI48 oscillator power consumption	-	-	312	350(2)	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.

Figure 21. HSI48 oscillator accuracy characterization results



Low-speed internal (LSI) RC oscillator

Table 44. LSI oscillator characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DDA(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 45* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 45. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
f_{PLL_IN}	PLL input clock(1)	1(2)	8.0	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	48	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
$Jitter_{PLL}$	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = - 40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = - 40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = - 40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 53. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor (3)	$V_{IN} = V_{SS}$	25	40	55	kΩ
R_{PD}	Weak pull-down equivalent resistor(3)	$V_{IN} = - V_{DDIOx}$	25	40	55	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Data based on design simulation only. Not tested in production.
2. The leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to *Table 52: I/O current injection susceptibility*.
3. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 22* for standard I/Os, and in *Figure 23* for 5 V-tolerant I/Os. The following curves are design simulation results, not tested in production.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOx}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 21: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 21: Voltage characteristics*).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 54. Output voltage characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OL}	Output low level voltage for an I/O pin	TTL port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		2.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–1.3	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 6 mA $V_{DDIOx} \geq 2$ V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OL}(4)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 4 mA	-	0.4	V
V_{OH}(4)	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	V
V_{OLFm+}(3)	Output low level voltage for an FTf I/O pin in Fm+ mode	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
		$\|I_{IO}\|$ = 10 mA	-	0.4	V

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 21: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Data based on characterization results. Not tested in production.
4. Data based on characterization results. Not tested in production.

Input/output AC characteristics

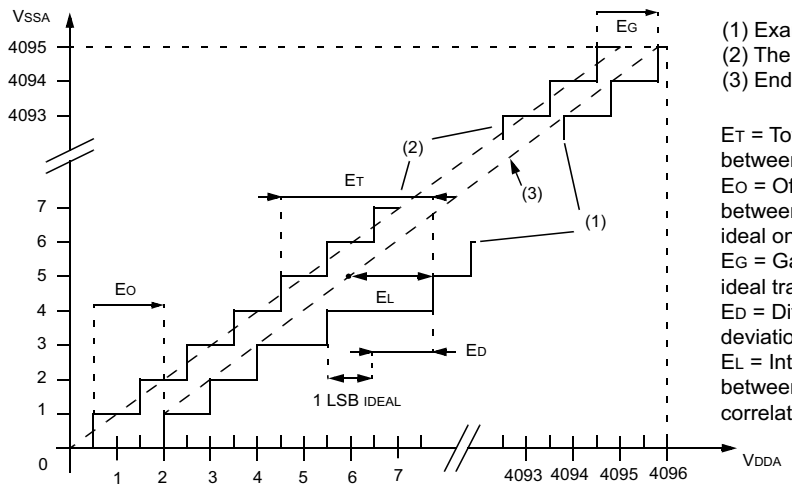
The definition and values of input/output AC characteristics are given in *Figure 24* and *Table 55*, respectively. Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 55. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] value(1)	Symbol	Parameter	Conditions	Min	Max	Unit
x0	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} \geq 2$ V	-	2	MHz
	$t_{f(IO)out}$	Output fall time		-	125	ns
	$t_{r(IO)out}$	Output rise time		-	125	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} < 2$ V	-	1	MHz
	$t_{f(IO)out}$	Output fall time		-	125	ns
	$t_{r(IO)out}$	Output rise time		-	125	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} \geq 2$ V	-	10	MHz
	$t_{f(IO)out}$	Output fall time		-	25	ns
	$t_{r(IO)out}$	Output rise time		-	25	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DDIOx} < 2$ V	-	4	MHz
	$t_{f(IO)out}$	Output fall time		-	62.5	ns
	$t_{r(IO)out}$	Output rise time		-	62.5	
11	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, $V_{DDIOx} \geq 2.7$ V	-	50	MHz
			C_L = 50 pF, $V_{DDIOx} \geq 2.7$ V	-	30	
			C_L = 50 pF, 2 V ≤ V_{DDIOx} < 2.7 V	-	20	
			C_L = 50 pF, $V_{DDIOx} < 2$ V	-	10	
	$t_{f(IO)out}$	Output fall time	C_L = 30 pF, $V_{DDIOx} \geq 2.7$ V	-	5	ns
			C_L = 50 pF, $V_{DDIOx} \geq 2.7$ V	-	8	
			C_L = 50 pF, 2 V ≤ V_{DDIOx} < 2.7 V	-	12	
			C_L = 50 pF, $V_{DDIOx} < 2$ V	-	25	
	$t_{r(IO)out}$	Output rise time	C_L = 30 pF, $V_{DDIOx} \geq 2.7$ V	-	5	
			C_L = 50 pF, $V_{DDIOx} \geq 2.7$ V	-	8	
			C_L = 50 pF, 2 V ≤ V_{DDIOx} < 2.7 V	-	12	
			C_L = 50 pF, $V_{DDIOx} < 2$ V	-	25	

2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.14* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. Data based on characterization results, not tested in production.

Figure 26. ADC accuracy characteristics

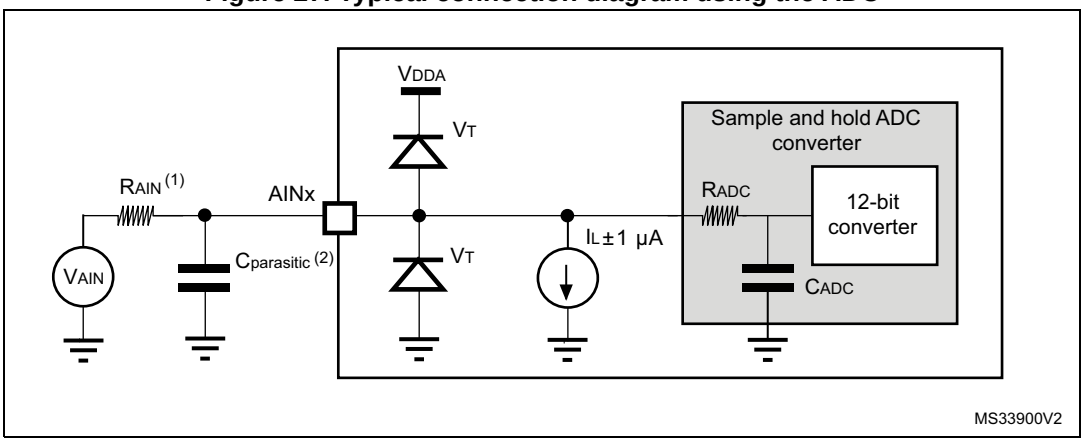


(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

MS19880V2

Figure 27. Typical connection diagram using the ADC



MS33900V2

1. Refer to *Table 57: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 13: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.17 DAC electrical specifications

Table 60. DAC characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage for DAC ON	2.4	-	3.6	V	-
R_{LOAD}(1)	Resistive load with buffer ON	5	-	-	kΩ	Load connected to V_{SSA}
		25	-	-	kΩ	Load connected to V_{DDA}
R_O(1)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(1)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer ON	-	-	V_{DDA} – 0.2	V	
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{DDA} – 1LSB	V	
I_{DDA}(1)	DAC DC current consumption in quiescent mode(2)	-	-	600	µA	With no load, middle code (0x800) on the input
		-	-	700	µA	With no load, worst code (0xF1C) on the input
DNL(3)	Differential non linearity Difference between two consecutive code-1LSB)	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
		-	-	±2	LSB	Given for the DAC in 12-bit configuration
INL(3)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration
		-	-	±4	LSB	Given for the DAC in 12-bit configuration
Offset(3)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{DDA}/2)	-	-	±10	mV	-
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{DDA} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{DDA} = 3.6 V

6.3.19 Temperature sensor characteristics

Table 62. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L (1)	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{30}	Voltage at 30 °C (± 5 °C)(2)	1.34	1.43	1.52	V
t_{START} (1)	ADC_IN16 buffer startup time	-	-	10	µs
t_{S_temp} (1)	ADC sampling time when reading the temperature	4	-	-	µs

1. Guaranteed by design, not tested in production.
2. Measured at V_{DDA} = 3.3 V ± 10 mV. The V_{30} ADC conversion result is stored in the TS_CAL1 byte. Refer to *Table 3: Temperature sensor calibration values*.

6.3.20 V_{BAT} monitoring characteristics

Table 63. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	2 x 50	-	kΩ
Q	Ratio on V_{BAT} measurement	-	2	-	-
Er(1)	Error on Q	–1	-	+1	%
t_{S_vbat} (1)	ADC sampling time when reading the V_{BAT}	4	-	-	µs

1. Guaranteed by design, not tested in production.

6.3.21 Timer characteristics

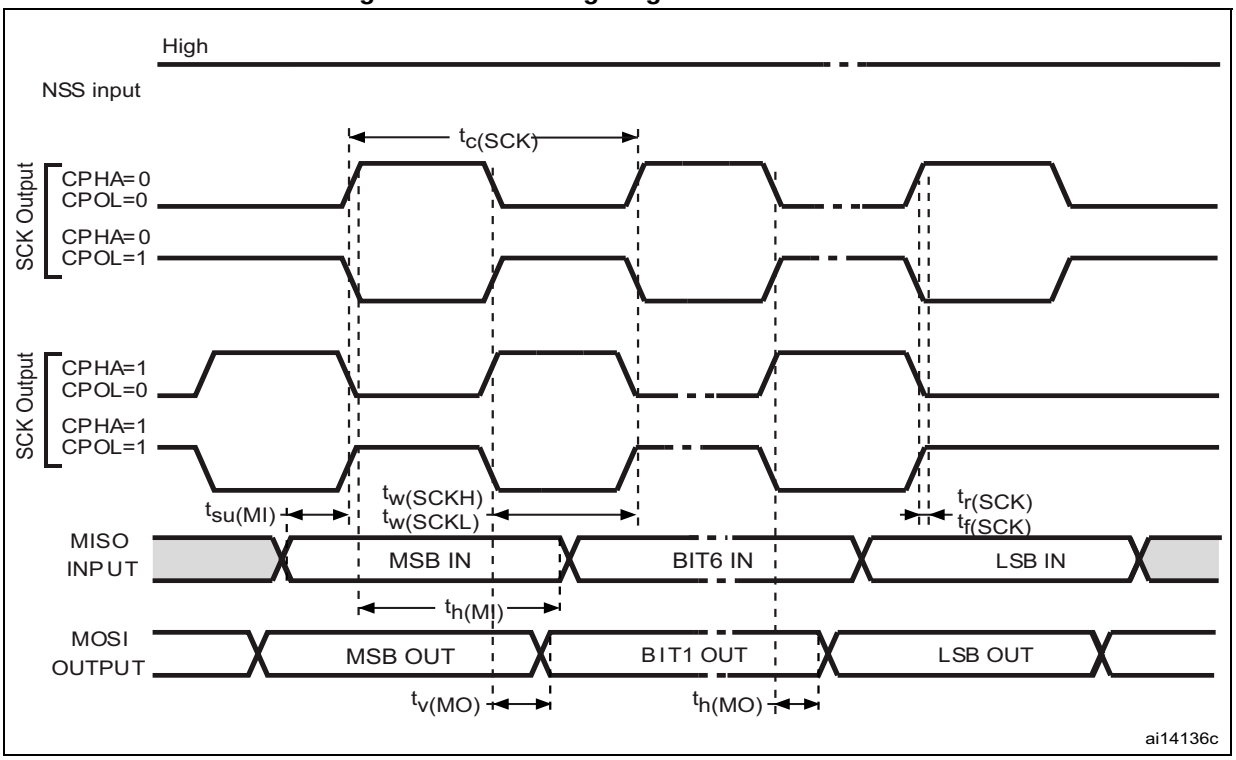
The parameters given in the following tables are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 64. TIMx characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	20.8	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	-	$f_{TIMxCLK}/2$	-	MHz
		$f_{TIMxCLK}$ = 48 MHz	-	24	-	MHz
t_{MAX_COUNT}	16-bit timer maximum period	-	-	2^{16}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	1365	-	µs
	32-bit counter maximum period	-	-	2^{32}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	89.48	-	s

Figure 30. SPI timing diagram - master mode



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Table 69. I^2S characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CK} $1/t_{c(CK)}$	I^2S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.597	1.601	MHz
		Slave mode	0	6.5	
$t_{r(CK)}$	I^2S clock rise time	Capacitive load C_L = 15 pF	-	10	ns
$t_{f(CK)}$	I^2S clock fall time		-	12	
$t_{w(CKH)}$	I^2S clock high time	Master f_{PCLK}= 16 MHz, audio frequency = 48 kHz	306	-	
$t_{w(CKL)}$	I^2S clock low time		312	-	
$t_{v(WS)}$	WS valid time	Master mode	2	-	
$t_{h(WS)}$	WS hold time	Master mode	2	-	
$t_{su(WS)}$	WS setup time	Slave mode	7	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
DuCy(SCK)	I^2S slave input clock duty cycle	Slave mode	25	75	%

Table 70. UFBGA100 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 34. Recommended footprint for UFBGA100 package

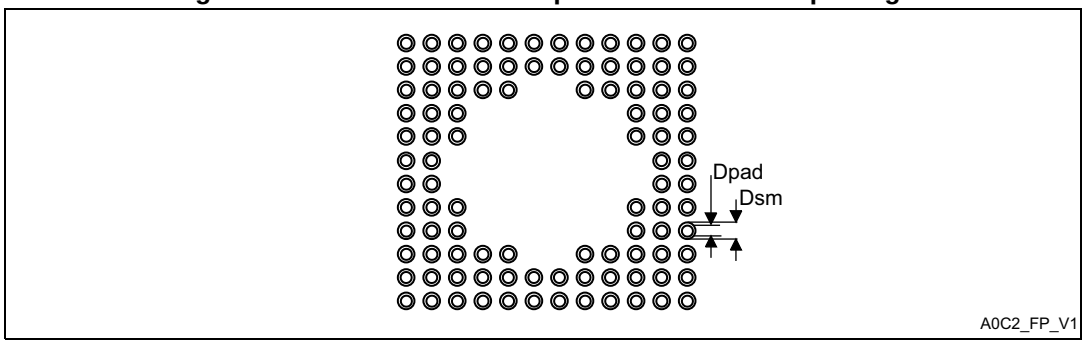


Table 71. UFBGA100 recommended PCB design rules

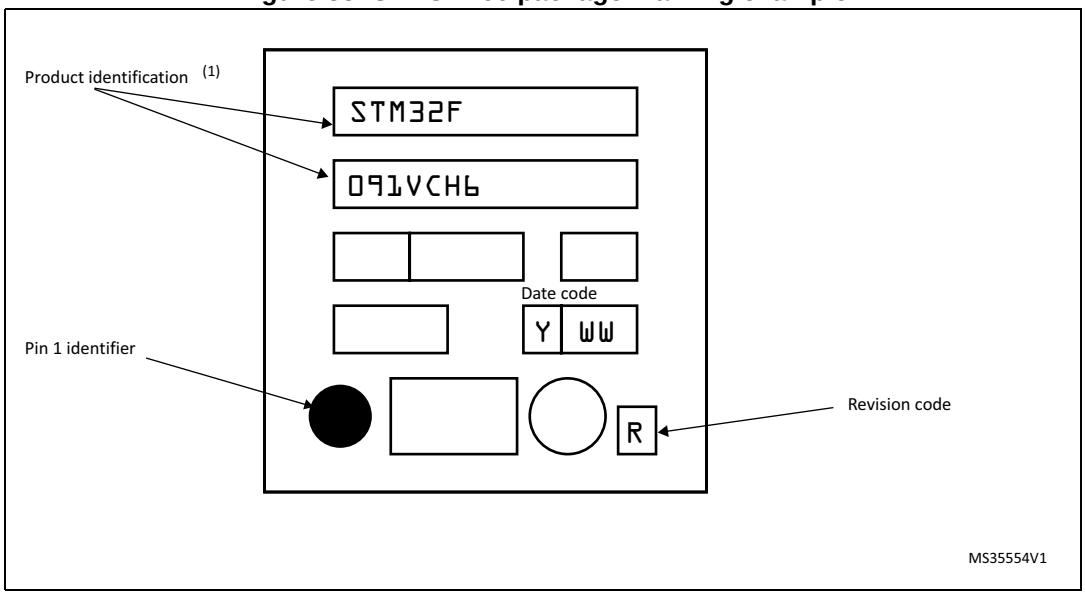
Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 35. UFBGA100 package marking example



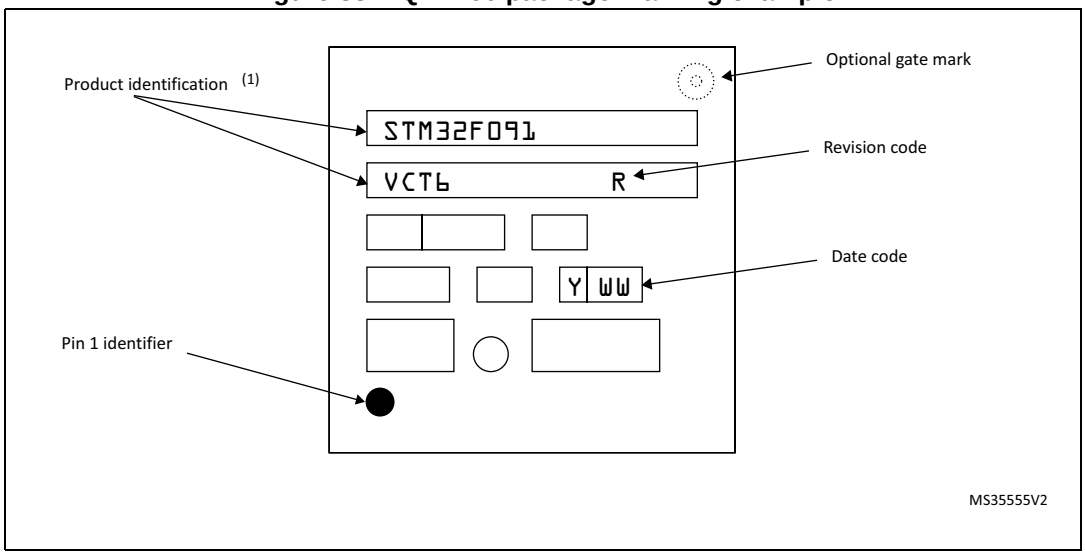
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 38. LQFP100 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 73. UFBGA64 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 40. Recommended footprint for UFBGA64 package

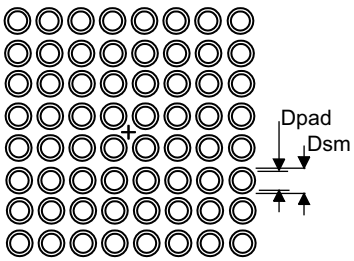


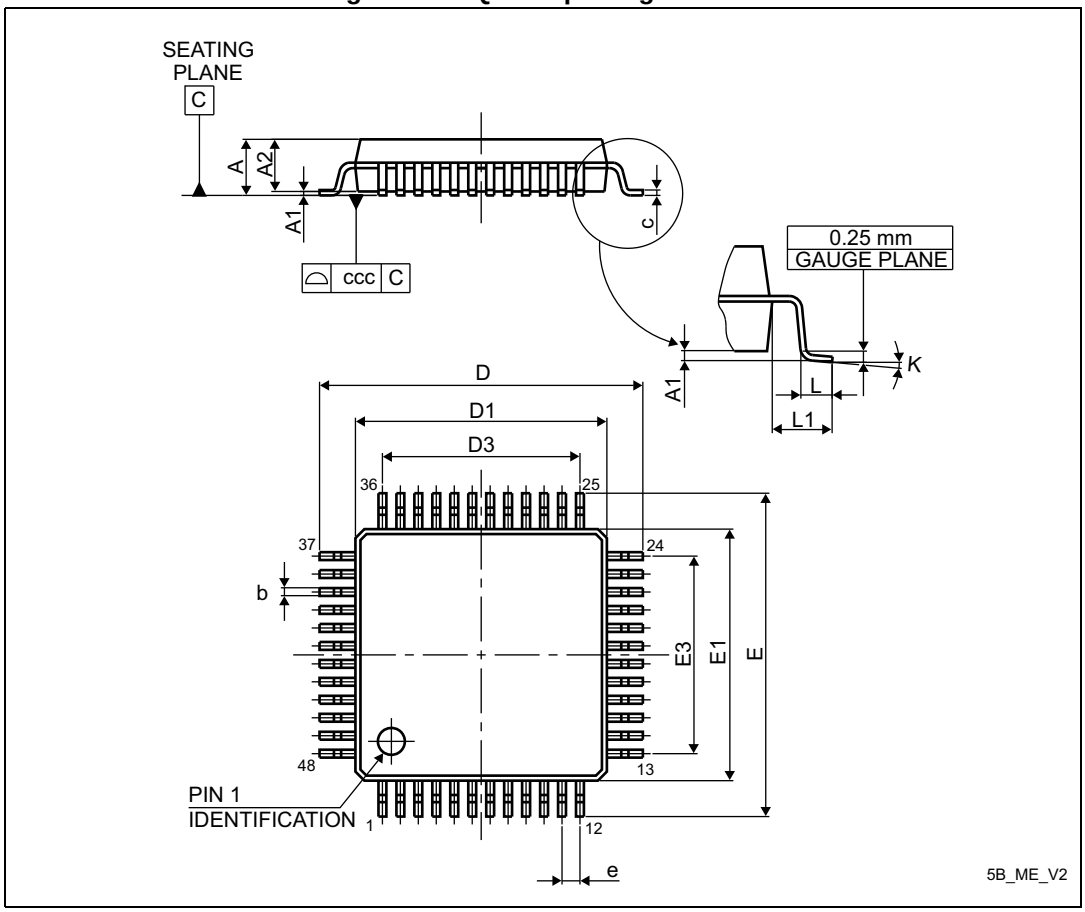
Table 74. UFBGA64 recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

7.6 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

Figure 48. LQFP48 package outline



1. Drawing is not to scale.